

IN THE CLAIMS:

1. (Currently Amended) A semiconductor device comprising:

a semiconductor IC chip provided with an electrode pad comprising a plurality of electrode pads, said pads each having a side;

an insulating layer formed located on a surface of the semiconductor IC chip, on the side of a surface of each of the electrode pads;

a connecting terminal on an outer surface of the insulating layer; and

a conductive post extending through the insulating layer and connecting the electrode pad of the semiconductor IC chip to the connecting terminal; terminal,

wherein the insulating layer is formed of comprises an insulating elastic material and the conductive post comprises a conductive elastic material.

2. (Canceled)

Serial No.: 10/619,551

3. (Currently Amended) The semiconductor device according to claim 21, wherein

the conductive elastic material of the conductive post contains conducting post comprises a synthetic rubber and conductive particles dispersed in the synthetic rubber.

4. (Currently Amended) The semiconductor device according to claim 3, wherein

the conductive elastic material of the conductive post is comprises a composite paste containing comprising an addition-polymerized silicone rubber, and at least 70% by weight or above Ag particles dispersed in the addition-polymerized silicone rubber, and

the composite paste as when cured has a volume resistivity of not more than  $5 \times 10^{-3}$   $\Omega \cdot \text{cm}$  or below.

5. (Currently Amended) The semiconductor device according to claim 1, wherein further comprising:

a wiring layer is formed located between the an electrode pad of the semiconductor IC chip and the conductive post.

6. (Currently Amended) The semiconductor device according to claim 1, wherein further comprising:

a wiring part is formed located between the connecting terminal and the conductive post.

7. (Original) The semiconductor device according to claim 1, wherein the connecting terminal is a solder ball.

8. (Currently Amended) The semiconductor device according to claim 7, wherein further comprising:

a barrier metal layer is provided located between the solder ball and the conductive post.

9. (Currently Amended) The semiconductor device according to claim 1, wherein

the insulating elastic material of the insulating layer is any one selected from the group consisting of silicone rubber, fluororubber, polyurethane rubber, polybutadiene rubber,

Serial No.: 10/619,551

acrylonitrile-butadiene copolymer and polyisoprene rubber, and has an elastic modulus of not more than 100 MPa or below.

10. (Currently Amended) The semiconductor device according to claim 1, wherein further comprising:

a protective layer on the outer surface of the insulating layer of the insulating elastic material is coated with a protective layer of the insulating layer, and a part of the connecting terminal lies comprises a portion located at a position on the protective layer.

11. (Currently Amended) The semiconductor device according to claim 10, wherein

the protective layer is formed of comprises a material selected from the group consisting of a polyimide resin, a liquid crystalline polymer or and an epoxy solder resist.

Serial No.: 10/619,551

12. (Currently Amended) The semiconductor device according to claim 1, wherein comprising:

the semiconductor device is a wafer-level chip-scale package produced by cutting a wafer with into a plurality of semiconductor IC chips.

13.-17. (Canceled)